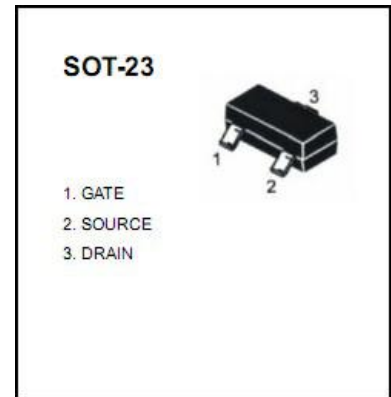
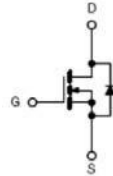


## SOT-23 Plastic-Encapsulate Transistors

### SYKJ2302-2.5A MOSFET(N-Channel)

#### FEATURES

TrenchFET Power MOSFET



MARKING: A2SHB

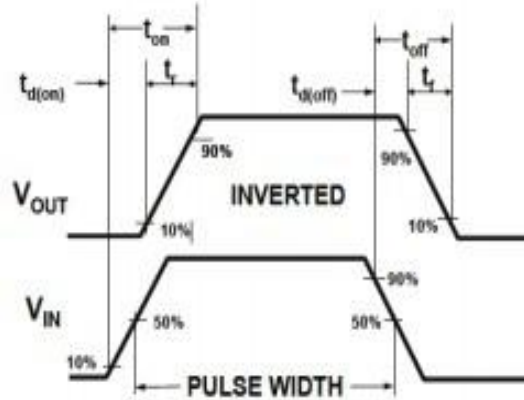
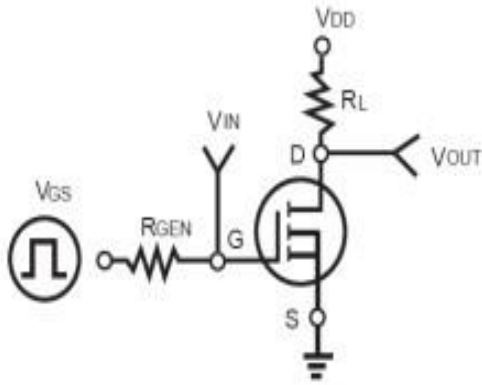
MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-Source voltage	20	V
V <sub>GS</sub>	Gate-Source voltage	±12	V
I <sub>D</sub>	Drain current	2.5	A
P <sub>D</sub>	Power Dissipation	0.9	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20			V
Gate-Threshold Voltage	V <sub>th(GS)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 uA	0.5	0.75	1.2	V
Gate-body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±10V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	uA
Drain-Source On-Resistance	r <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =2A		58	82	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.5A		43	59	mΩ
Forward Trans conductance	g <sub>fs</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =2.9A		9.5		s
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz		280		pF
Output Capacitance	C <sub>oss</sub>			60		
Reverse Transfer Capacitance	C <sub>rss</sub>			40		
Switching Capacitance						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =2.5A, V <sub>GS</sub> =4.5V, R <sub>GEN</sub> =2.8Ω		6		nS
Turn-on Rise Time	t <sub>r</sub>			5		
Turn-off Delay Time	t <sub>d(off)</sub>			9		
Turn-off Fall Time	t <sub>f</sub>			1.5		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =2.5A, V <sub>GS</sub> =4.5V,		1.7		nC
Gate-Source Charge	Q <sub>gs</sub>			0.3		
Gate-Drain Charge	Q <sub>gd</sub>			0.8		
Drain-Source Diode Characteristics						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =2.5A			1.2	V
Diode Forward Current	I <sub>S</sub>				2.5	A

Switch Time Test Circuit and Switching Waveforms:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Power Dissipation

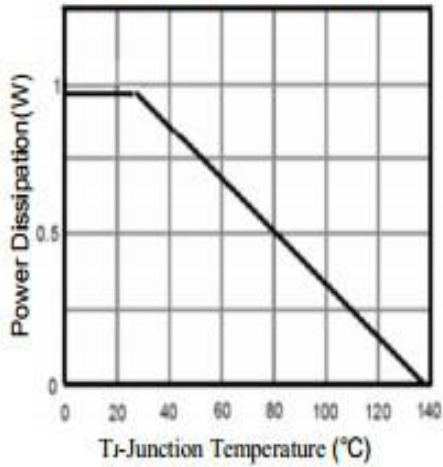


Figure2. Drain Current

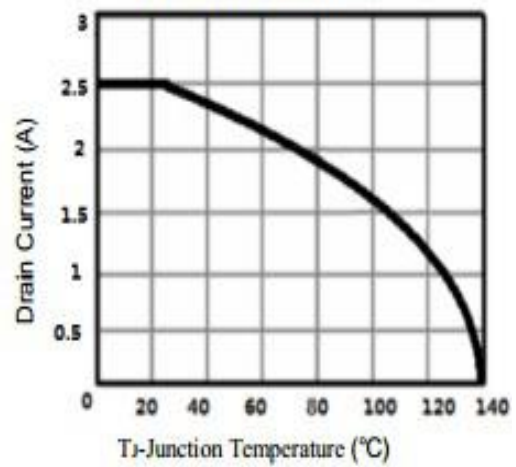


Figure3. Output Characteristics

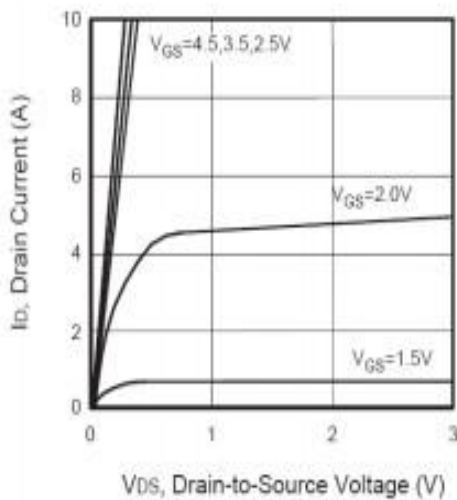
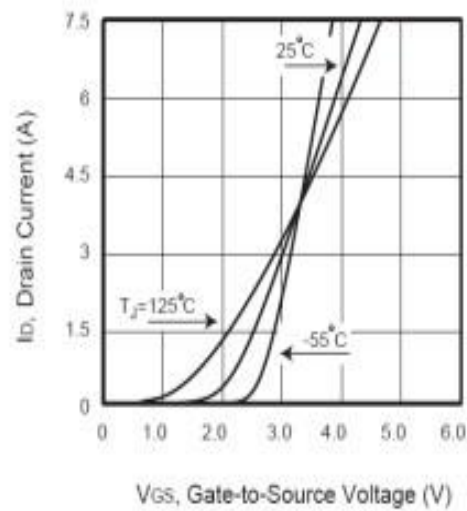


Figure4. Transfer Characteristics



声明:

双宜科技保留电路及其规格书的更改权, 以便为客户提供更优秀的产品, 规格若有更改, 恕不另行通知。

双宜科技公司一直致力于提高产品的质量和可靠性, 然而, 任何半导体产品在特定条件下都有一定的失效或发生故障的可能, 客户有责任在使用双宜产品进行产品研发时, 严格按照对应规格书的要求使用双宜产品, 并在进行系统设计和整机制造时遵守安全标准并采取安全措施, 以避免潜在失败风险造成人身伤害或财产损失等情况。如果因为客户不当使用双宜产品而造成的人身伤害、财产损失等情况, 双宜公司不承担任何责任。

本产品主要应用于消费类电子产品中, 如果客户将本产品应用于医疗、军事、航天等要求极高质量、极高可靠性的领域的产品中, 其潜在失败风险所造成的人身伤害、财产损失等情况, 双宜科技不承担任何责任。

本规格书所包含的信息仅作为双宜产品的应用指南, 没有任何专利和知识产权的许可暗示, 如果客户侵犯了第三方的专利和知识产权, 双宜科技不承担任何责任。

## 客户服务中心

深圳市双宜科技有限公司

电话: 0755-27863192

手机: 13823527686

网址: [www.ledfangan.com](http://www.ledfangan.com)